G round state properties of ferrom agnetic m etal/conjugated polym er interfaces

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A bstract

We theoretically investigate the ground state properties of ferrom agnetic m etal/conjugated polymer interfaces. The work is partially motivated by recent experiments in which injection of spin polarized electrons from ferrom agnetic contacts into thin Im s of conjugated polymers was reported. We use a one-dim ensional nondegenerate Su-Schrie er-Heeger (SSH) Ham iltonian to describe the conjugated polymer and one-dimensional tight-binding models to describe the ferrom agnetic m etal. We consider both a model for a conventional ferrom agnetic m etal, in which there are no explicit structural degrees of freedom, and a model for a half-metallic ferromagnetic colossal magnetoresistance (CMR) oxide which has explicit structural degrees of freedom. The Ferm ienergy of the magnetic metallic contact is adjusted to control the degree of electron transfer into the polymer. We investigate electron charge and spin transfer from the ferrom agnetic metal to the organic polymer, and structural relaxation near the interface. Bipolarons are the lowest energy charge state in the bulk polymer for the nondegenerate SSH model Hamiltonian. As a result electrons (or holes) transferred into the bulk of the polym er form spinless bipolarons. However, there can be spin density in the polymer localized near

the interface.

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I. IN TRODUCTION

Magnetoelectronics or spintronics is a eld of growing interest. Since the discovery of giant magnetoresistance (GMR) [1], rapid progress has been made in this eld. Electron spin injection and spin dependent transport are essential aspects of spintronics and have been extensively studied in a number of di erent contexts including: ferrom agnetic metals to superconductors [2]; ferrom agnetic metals to normal metals [3]; ferrom agnetic metals to nonmagnetic semiconductors [4] and magnetic semiconductors to nonmagnetic semiconductors [5]. Recently, spin polarized injection and spin polarized transport in conjugated polymers have been reported [6]. Specically, spin injection was observed into thin in sof the conjugated organic material sexithingly from halfmetallic manganites (in which electron spins at the Fermi surface are completely polarized) at room temperature. The ease of fabrication and low temperature processing of conjugated organic materials open many application possibilities, and electronic as well as opto-electronic devices fabricated from these materials, e.g. organic light-emitting diodes and spin valves, are being actively pursued [6].

Theoretical study of spin polarized in jection and transport has been carried out prim arily in the fram ework of classical transport equations [7{9]. The role of interface properties for spin in jection in inorganic sem iconductors was investigated in this context [10{13]. The purpose of this paper is to study the ground state characteristics such as lattice displacements, charge density and spin density distribution of conjugated organic polymers contacted with a ferromagnetic metal. An added motivation to study this type of \active" interface is that because of relatively large electron-phonon coupling the materials on both sides of the interface can deform, which may facilitate spin polarized in jection.

The paper is organized as follows. In the next section we present tight-binding models for a nondegenerate conjugated polymer, a ferrom agnetic (FM) metal, a half-metallic colossal magnetoresistance (CMR) material and the interface between the polymer and the two kinds of magnetic materials. Section III presents the results for a model junction between the polymer and the FM metal, and Sec. IV describes results for CMR/polymer junctions.

Our main ndings are sum marized in Sec. V.

II.M ODEL

O rganic polym ers currently used for electronic and opto-electronic devices typically have a nondegenerate ground state. The rst experim ental evidence of spin polarized electrical injection and transport in conjugated organic materials was carried out using sexithienyl (Γ_6), a -conjugated oligom er [6,14]. The underlying physics of spin injection and transport is of particular interest for conjugated organic materials, where strong electron-phonon coupling leads to polaronic (or bipolaronic) charged states [15]. These polymers or oligomers have chain structures that can be described using a nondegenerate version of the one-dimensional SSH model, the Brazovskii-K irova (BK) model [16,17],

$$H_{P} = \begin{pmatrix} X & & X \\ & P & a_{i}^{+}, & a_{i}; & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & &$$

where $a_{i,}^+$ ($a_{i,}$) denotes the electron creation (annihilation) operator at site i with spin , $_P$ is the on-site electron energy of an atom , t_P is the transfer integral in a uniform (undim erized) lattice and $_P$ the electron-phonon interaction parameter, t_1 introduces nondegeneracy into the polymer, and K_P denotes a spring constant.

To describe a conventional ferrom agnetic m etalwe use a one-dim ensional tight-binding model with kinetic energy (H_{ke}) and spin splitting (H_{Hund}) term s:

$$H_{FM} = H_{ke} + H_{Hund}; \qquad (2)$$

$$H_{ke} = \int_{i;}^{X} t_{F} (a_{i;}^{+} a_{i+1}; + a_{i+1}^{+}; a_{i;});$$
(3)

$$H_{H und} = \int_{i}^{X} J_{i}(a_{i;"}^{+}a_{i;"} a_{i;"} a_{i;\#}); \qquad (4)$$

where t_F is the transfer integral for a ferrom agnetic m etal and H $_{\rm H\ und}$ describes the spin splitting of the magnetic atom with site-dependent strength J_i . We take an occupation of

one electron per atom and $J_i = J_M$ with parameters $t_F = 0.622$ eV and $J_M = 0.625$ eV for the conventional ferrom agnetic m etal.

CMR materials can form half-metallic ferromagnets and are therefore very interesting as spin polarized electron in jecting contacts. CMR materials have a chemical composition such as Re_{1 x}A k_x M nO₃, where Re represents a rare earth atom, e.g. La and Nd, and Ak represents an alkalimetal such as Ca, Sr and Ba. Mn has a valence of (3 + x) which depends on the doping concentration x. Depending on doping, the material can be either a metal or an insulator and either ferrom agnetic or antiferrom agnetic [18]. In particular, $Re_{1} xAk_{x}MnO_{3}$ can be a half-m etallic ferrom agnet when 0.2 < x < 0.5, for example, with Re=La and Ak=Ca. In this state all the electrons at the Ferm i surface have the sam e spin orientation. The M n atom has 5 electrons in its 3d orbitals. These electrons have a parallel spin alignment due to a strong Hund's rule splitting. Because of crystal eld splitting in a solid, three of the orbitals form the low energy t_{2q} states, xy; yz and zx, and the other two form the higher energy e_g states, x^2-y^2 and $3z^2-r^2$. In the ground state, the electrons in t_{2g} are localized and constitute core spins. The e_q states are extended and the electrons in these states can be delocalized. In cubic symmetry, the two e_q levels are degenerate. However in tetragonal or orthorhombic symmetry, the degeneracy of e_q is broken by a Jahn-Teller coupling due to the electron-lattice interaction, which causes movement of oxygen ions with respect to the manganese ions.

Here, we suppose for sim plicity that a polymer or oligomer chain is connected at the ends of a CMR lattice in the z-direction. We consider a one-dimensional model which contains the basic properties of a half-metallic CMR material; a ferromagnetic metal with electron-lattice coupling. The following one-dimensional model captures these essential features,

$$H_{CMR} = H_{ke} + H_{Hund} + H_{el lat} + H_{elastic};$$
 (5)

where H_{ke} and H_{Hund} are given in Eqs. (3) and (4), and

$$H_{el lat} = X_{F (u_{i+1} u_i)a_{i;}^+ a_{i;}^+} (a_{i}, a_{i}, a_{i})$$
 (6)

$$H_{\text{elastic}} = \frac{X}{2} \frac{1}{2} K_F \left[(i_1 u_i)^2 + (u_{i+1} i)^2 \right]; \tag{7}$$

Here u_i and i are the displacements of the ith oxygen atom and manganese atom, respectively. H_{ke} describes electron hopping between two nearest manganese atoms. H_{H und} describes the spin splitting of a magnetic manganese atom that results from interaction with the core spins. We have $J_i = J_M$ for the ferromagnetic state (core spins aligned) and $J_i = (1)^i J_M$ for the antiferromagnetic state. H_{el lat} gives the on-site energy of the manganese atoms, which depends on the displacement of the nearest neighbor oxygen atoms, and F denotes the electron-lattice coupling strength. The last term H_{elastic} represents the elastic energy and includes nearest neighbor interactions.

Coupling at the interface between the conjugated polymer and the ferrom agnetic metal is described by the hopping integral,

$$t_{FP} = (t_{FP} + t_{PP}) = 2;$$
 (8)

where is a weighting parameter. In principle, this coupling could be spin-dependent, but here we take $t_F^{"}_{P} = t_F^{\#}_{P} = t_F^{\#}_{P}$ for simplicity. Periodic boundary conditions are adopted.

The param eters used for the CMR contact Re $_1$ xAkxM nO $_3$ are $t_F=0.622$ eV, $J_M=1.25$ eV, $K_F=7.4$ eV/A $_2^2$ [19] and $t_F=2.0$ eV/A. For the organic polymer we take representative param eters as $t_P=2.5$ eV, $t_P=4.2$ eV/A, $t_P=21.0$ eV/A $_2^2$ [20]. We set the degeneracy breaking param eter $t_1=0.04$ eV so that the energy difference is $t_A=0.035$ eV per carbon atom between the two dimerized phases. The relative chemical potential $t_P=0.035$ eV per carbon adjust the electron transfer between the ferrom agnet and the polymer. Segment lengths were taken so that Re $t_A=0.035$ eV per carbon 0 monits, that is $t_A=0.035$ eV per carbon 0 monits, that is $t_A=0.035$ eV per carbon 0 monits, that is $t_A=0.035$ eV per carbon 0 monits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 monits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 monits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 monits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 monits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 mits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 mits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 monits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 monits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 monits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 monits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 monits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 mits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 mits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 mits and the polymer 100 of CH 0 mits, that is $t_A=0.035$ eV per carbon 0 mits and the polymer 100 of CH 0 mits and the polymer 100 o

W e $\,$ rst study an isolated R e $_xA\,k_xM$ nO $_3$ chain to test the e $\,$ ectiveness of this model for the CM R m aterial. The electronic eigenstates

$$j > = {X \atop i} Z_{i;}, a_{i;}^{+} j >$$
 (9)

corresponding to the eigenvalue "; are solved from the equation,

$$t_F Z_{i+1}$$
; $t_F Z_{i-1}$; $J_i Z_{i}$; $F(u_{i+1} u_i) Z_{i}$; $= ", Z_{i}$; (10)

where = +1 for spin up and 1 for spin down. The displacements f_{ig} and fu_{ig} in the ground state are determined from the eigenstates self-consistently:

$$_{i} = \frac{1}{2} (u_{i} + u_{i+1});$$
 (11)

If $_{\rm F}$ = 0, the stable con guration has a uniform structure, i.e. $_{\rm i}$ = 0 and $u_{\rm i}$ = 0, without distortion. O therwise, some distortion will occur. From Eqs. (11) and (12) we see that the displacements of both oxygen and manganese atoms depend on the electronic density at the manganese atoms.

The structure and magnetism of Re $_{1}$ $_{x}$ Ak $_{x}$ M nO $_{3}$ depend on the doping concentration x which determ ines the electron number permanganese atom. The orbitals of each manganese atom have been renormalized to a single orbital in the present model and the electron number permanganese atom is denoted by y (1). Figure 1(a) shows the dependence of the energy dierence per site between the ferromagnetic (FM) and antiferromagnetic (AFM) states on y. For an electronic doping concentration y=0 (no electrons), the FM and AFM states have the same energy and the equilibrium conditions give $_{i}=u_{i}=0$. For y=1, that is each manganese atom having one electron, the AFM state is lower in energy than the FM state. An energy gap of 2.5 eV appears in the AFM state for both the spin up and down energy levels. The lower subband levels are occupied and the system is an insulator. At y=0.5, the FM state is lower in energy than the AFM state. At this electron concentration,

the energy dierence between FM and AFM states is 0.127 eV perm anganese atom. In this case, as shown in Fig. 1 (b), the energy bands of the FM state are totally spin split. There is a gap of 0.26 eV at the wavevector k==2a (a is the lattice constant between two nearest M n sites) and the system is an insulator. This gap can be adjusted by changing $_F$. When $_F$ 1.4 eV/A, the gap is close to zero. All the spin down levels are empty and only the lower sublevels of the spin up band are occupied. At y=0.5, the charge density has an oscillatory distribution. For example, at $_F=2.0$ eV/A, the densities on two adjacent manganese atoms are about 0.621e and 0.379e (at y=0.5). Away from y=0.5, the energy gap disappears and the system becomes a ferrom agnetic half-metal. In the ferrom agnetic state, the sites displace in the approximate pattern,

$$i = 0 \sin [2i(y \ 0.5)];$$
 (13)

$$u_i = u_0 \cos[2i(y \ 0.5)]$$
: (14)

With electron concentration $0.2~{\rm y}~0.45$, the displacements of both M n and 0 atoms become very small ($_0~0.005~{\rm A}~{\rm and}~{\rm u}_0~0.01~{\rm A}$) and decrease to zero when the chain length becomes arbitrarily long. That is, the system becomes uniform in this doping region, and correspondingly the charge density is also uniform with a half-metallic property. These results are consistent with the basic properties of the CMR materials [18] and show that the one-dimensional model gives a reasonable description of them.

III.FERROM AGNETIC METAL/POLYMER JUNCTION

We rst consider a polymer chain contacted by a simple rigid ferrom agnetic metal chain. In the case of half—lling for the parameters used, the spin polarization is = $(N_{"} N_{\#}) = (N_{"} N_{\#}) = (N_{"} N_{\#}) = 0.34$: The polymer has a one-dimensional chain structure with a strong electron-lattice interaction that will cause localized charged excitations. When the polymer is connected with a ferromagnetic metal, both the lattice conguration and charge distribution of the polymer are a ected. By adjusting the relative chemical potential, electrons (or holes)

are transferred into the polymer and cause the displacement of the lattice sites. Results are shown in Fig. 2 and Fig. 3 for $_{\rm P}$ = 0 and $_{\rm P}$ = 1:0 eV, respectively. Following the usual convention, in this paper the displacement is plotted with a multiplying factor (1)¹, where i is the site index. The ferrom agnetic metal is to the left and the polymer is to the right of the interface which is between sites n=100 and 101. In Fig. 2, there is no electron transfer between the segments, and the charge density is uniform within the whole system. But the charges near the interface can be spin polarized. The polarization oscillates and decays into the polymer segment. The decay length of the spin polarization is about 6b, where b is the lattice constant in the polymer. If the chemical potential of the ferrom agnet is higher than the bipolaron level in the polymer, as in Fig. 3, electrons are transferred into the polymer segment to reach a new equilibrium for the system. Instead of forming extended electronic waves, the extra electrons in the polymer form localized charged bipolarons. Figure 3 (a) shows the displacements of lattice sites, from which we see that, in this case, three complete bipolarons are formed within the polymer together with som e local distortions at the interface. The corresponding charge and spin distributions are shown in Fig. 3 (b). In the present BK model for the nondegenerate polymer, bipolarons are energetically lower than polarons. Since each bipolaron has two con ned electronic charges with opposite spins, a bipolaron has no spin. There is neither localized nor extended spin distribution within the polymer layer. Because the polymer is nonmagnetic in the ground state, or more generally at thermal equilibrium, there is no spin distribution far from the interface.

IV.FERROM AGNETIC CM R/POLYM ER JUNCTION

Here, we consider the polymer chain in contact with a half-metallic ferromagnetic Re_{1} $_{x}Ak_{x}M$ nO $_{3}$ chain with electron concentration y=0.32. By adjusting the relative chemical potential, electrons are transferred between the CMR material and polymer. At $_{p}=2.15$ eV, there is essentially no electron transfer between the segments. Figure 4(a)

shows the displacements of the atoms (Mn, O and C) compared to their uniform bulk positions. Within the CMR segment, both the manganese and oxygen atoms are only slightly displaced. The small displacements are due to the nite length of the segment and disappear as the segment length is increased. The carbon atoms have a displacement of 0.05 A, corresponding to the bulk dimerization of the polymer chain. The interfacial atoms have a deviation from the bulk dimerization, which results in a small expansion of the end bonds of the CMR segment and a contraction of the rst few polymer bonds. The charge and spin densities are shown in Fig. 4(b). Because the CMR material is completely spin polarized. the charge and spin densities coincide in this segment. The distributions of charge and spin density in each segment are uniform except for a small modulation near the interface. The m odulation in the CMR material is a nite size e ect discussed previously. There is neither a net charge nor spin distribution within the bulk polymer. When we increase the chemical potential of the CMR material, electrons are transferred into the polymer. The results for $_{\rm P}$ = 2:90 eV are shown in Fig. 5. At this value for the chemical potential, 6.11 electrons transfer to the polymer segment. The CMR segment keeps a nearly uniform lattice structure except a small deviation at the interface. In the polymer, from the displacements shown in Fig. 5(a), bipolaron states form. The localized electronic density can be seen more clearly in Fig. 5(b). Because the transferred electrons form spinless bipolarons, there is no spin am plitude within the polymer segment.

These results become more apparent if we exam in the change in electronic density of states (DOS) de ned by the Lorentz line shape formula

$$g(") = X \frac{1}{(" ")^2 + 2};$$
 (15)

where " is a one-electron energy eigenvalue and a phenomenological Lorentz line width, which we choose as = 0.15 eV. Figure 6(a) shows the DOS for the CMR/polymer chain before coupling of the two segments (that is, for the two separate material segments) and Fig. 6(b) shows the DOS after coupling. The relative chemical potential was adjusted to be $_{\rm P} = 2.15$ eV as in Fig. 4 so that there is no electron transfer between the CMR material

and polymer after coupling. From the gure we see that there is still a large gap for the spin down states, but the gap for spin up states decreases after coupling. All the occupied states near the Fermi level have spin up and these states are connect in the segment of the CMR material. Increasing the relative chemical potential $_{\rm P}=2.90~{\rm eV}$ as in Fig. 5, we plot the DOS before and after coupling in Fig. 7(a) and Fig. 7(b), respectively. Because the Fermi level of the CMR is above the bipolaron level of the polymer, electrons transfer to the polymer after coupling. They form double-charged bipolarons. The bipolaron levels are indicated in Fig. 7(b), where the levels of spin up and down states overlap (the spin up states of the bipolaron near 2.5 eV cannot be seen easily due to the large DOS caused by the CMR material). Thus, bipolarons have no spin. The difference in DOS of spin up and down at the bipolaron states arises from the elect of the CMR material at the interface.

V.CONCLUSIONS

O rganic (-conjugated) polymers di er from traditional inorganic sem iconductors due to their strong electron-lattice interactions. C arriers in (nondegenerate) polymers are not typically electrons or holes but rather charged polarons or bipolarons. In this paper we have studied the ground state properties of a ferrom agnetic metal/organic polymer junction. Two kinds of magnetic contacts were considered, a simple ferrom agnetic metal with fractional spin polarization and a CMR ferrom agnet with a half-metallic ground state. It was found that the electric charges in the polymer near the interface can have spin polarization. The spin density decays in an oscillatory fashion into the polymer. By adjusting the relative chemical potential, electrons can be transferred into the polymer from the magnetic layer through the interfacial coupling. The transferred electrons form bipolarons, which have no spin, so that there is no spin density in the bulk of the polymer. The polymer is nonmagnetic and in the ground state, or more generally at them all equilibrium, there will not be a spin polarization in this material far from the interface.

The present model is simple and only static characteristics were investigated. In addition,

the model is one-dimensional and Coulomb interactions between electrons were not included so that there was no Schottky elect at the interface. But major factors have been included, such as lattice relaxation and interfacial coupling. The main motivation for this model came from recent polarized spin injection (and spin-coherent transfer) experiments on the conjugated organic oligomer exithienyl (thin lm) in which a half-metallic ferromagnetic CMR contact was used [6]. This oligomer can serve as an active transport material for potential organic opto-electronic and spintronic devices. Dynamics under external bias will be studied to describe spin injection and polarized spin transport in conjugated organic materials, but an understanding of ground state properties is required to initiate a study of such dynamics.

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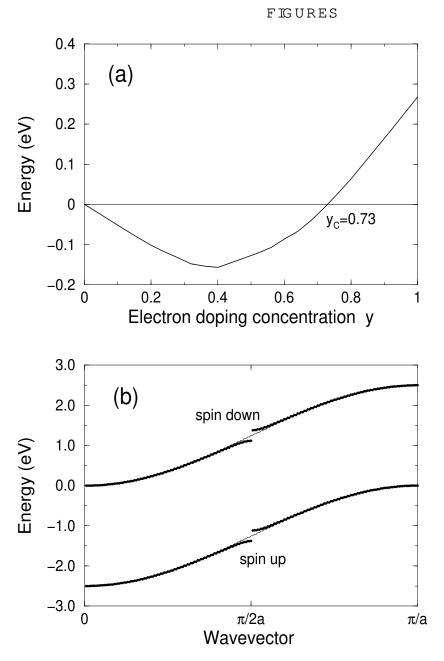


FIG.1. (a) Dependence of energy dierence per site between a one-dimensional ferrom agnetic chain and an antiferrom agnetic $Re_{1-x}Ak_{x}M$ nO chain with doping concentration y. (b) Energy levels of $Re_{1-x}Ak_{x}M$ nO in the ferrom agnetic state: y=0.5 (thick line) and y=0.32 (thin line). The upper curve in panel (b) is for spin down electrons and the lower curve is for spin up electrons. A gap of 0.26 eV appears at k=-2a in the case of half doping (y=0.5).

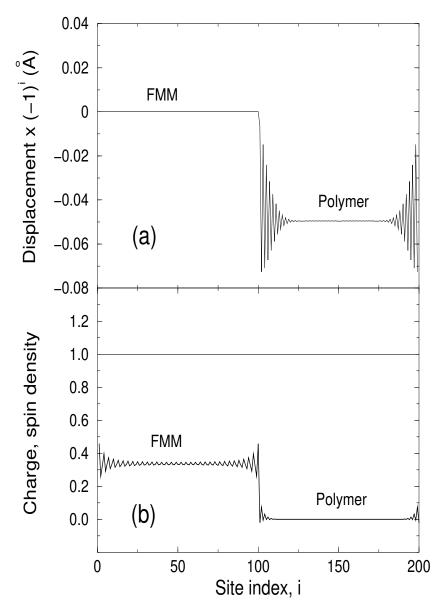


FIG .2. For a simple ferrom agnetic metal (FMM)/polymer chain: (a) Site displacements; (b) charge (thin line) and spin (thick line) density distributions. There is no electron transfer between the FMM and the polymer. The interface is between sites 100 and 101 and $_{\rm P}=0$. All the site displacements are plotted after multiplying with a factor ($_{\rm I}$), where i is the site index.

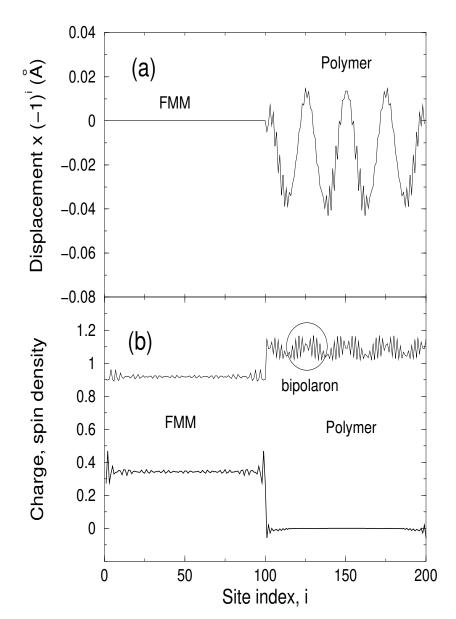


FIG.3. Same as in Fig. 2 but for $_{\rm P}$ = 1:0 eV.E lectrons are transferred from the FM M to the polym er through the interface by increasing the chem ical potential of the FM M , resulting in bipolarons form ing in the polym er.

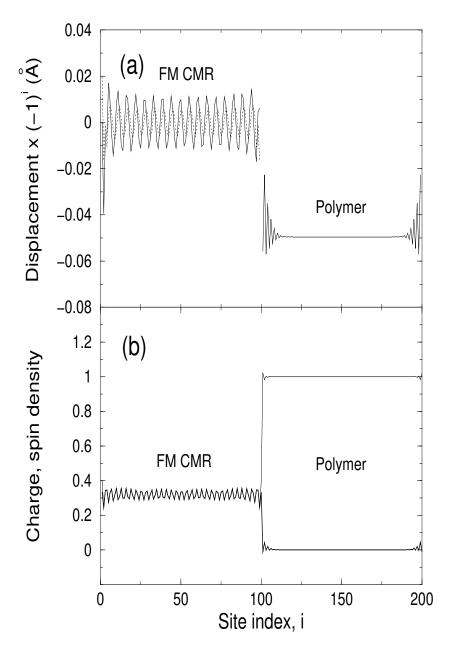


FIG. 4. For a ferrom agnetic $Re_{1-x}Ak_xM$ no (FM CMR)/polymer chain: (a) Site displacements of Mn (left dotted), O (left solid) and C (right solid) atoms; (b) charge (thin line) and spin (thick line) density distributions. The charge and spin densities coincide in the CMR material. There is no electron transfer between the FMM and the polymer. The interface is between sites 100 and 101.

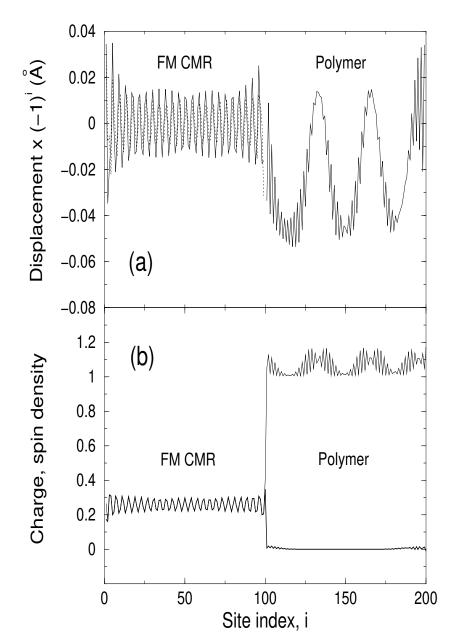


FIG.5. Same as in Fig. 4 but with some electrons transferred from the FM CMR segment to the polymer through the interface by increasing the chemical potential of the FM CMR material, resulting in bipolarons forming in the polymer.

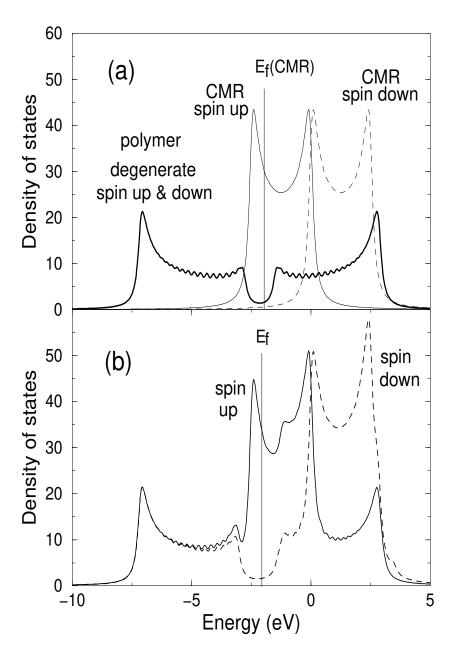


FIG. 6. Density of states of the FM CMR material and the polymer: (a) before coupling and (b) after coupling. The thick solid line in (a) is for both spin up and spin down electrons in the polymer, the thin solid (dashed) line in (a) is for spin up (spin down) electrons in the polymer. The solid (dashed) line in (b) is for spin up (spin down) electrons. The phenomenological Lorentz width is = 0.15. The Fermi level of the CMR material lies below the bipolaron energy of the polymer, so that there is no signicant electron transfer.

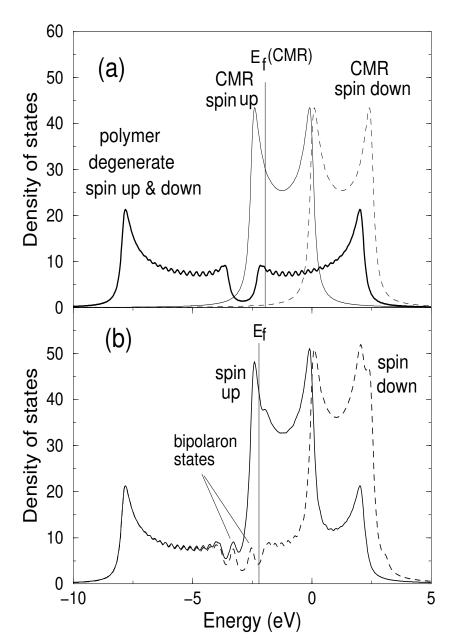


FIG. 7. Same as in Fig. 6 but with the Ferm i level of the CMR material higher than the bipolaron energy of the polymer, so that electrons transfer from the CMR segment to the polymer after coupling.